

N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

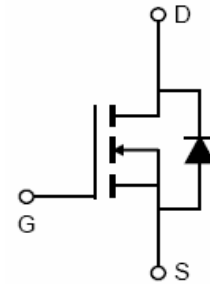
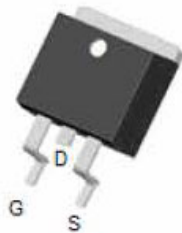
- $V_{DS} = 100V, I_D = 120A$
 $R_{DS(on)} = 4.6m\Omega$, typical (TO-263) @ $V_{GS} = 10V$
 $R_{DS(on)} = 4.7m\Omega$, typical (TO-220) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED!
100% ΔV_{ds} TESTED!

TO-220



TO-263



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HMS120N10	HMS120N10	TO-220	-	-	-
HMS120N10D	HMS120N10D	TO-263	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	120	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	84	A
Pulsed Drain Current	I_{DM}	360	A
Maximum Power Dissipation	P_D	200	W
Derating factor		1.33	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	1050	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.75	$^{\circ}\text{C/W}$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100		-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	
On Characteristics ^(Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =70A	TO-263	-	4.6	6.0	mΩ
			TO-220		4.7	6.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =70A		90	-	S	
Dynamic Characteristics ^(Note4)							
Input Capacitance	C _{iss}	V _{DS} =40V, V _{GS} =0V, F=1.0MHz	-	4950	-	PF	
Output Capacitance	C _{oss}		-	850	-	PF	
Reverse Transfer Capacitance	C _{rss}		-	40	-	PF	
Switching Characteristics ^(Note 4)							
Turn-on Delay Time	t _{d(on)}	V _{DD} =40V, I _D =70A V _{GS} =10V, R _G =1.6Ω	-	18	-	nS	
Turn-on Rise Time	t _r		-	11	-	nS	
Turn-Off Delay Time	t _{d(off)}		-	38	-	nS	
Turn-Off Fall Time	t _f		-	9	-	nS	
Total Gate Charge	Q _g	V _{DS} =40V, I _D =70A, V _{GS} =10V	-	88	-	nC	
Gate-Source Charge	Q _{gs}		-	22		nC	
Gate-Drain Charge	Q _{gd}		-	25		nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =70A	-		1.2	V	
Diode Forward Current ^(Note 2)	I _S		-	-	120	A	
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 70A di/dt = 100A/μs ^(Note3)	-	72	-	nS	
Reverse Recovery Charge	Q _{rr}		-	102	-	nC	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=40V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$

Typical Electrical and Thermal Characteristics

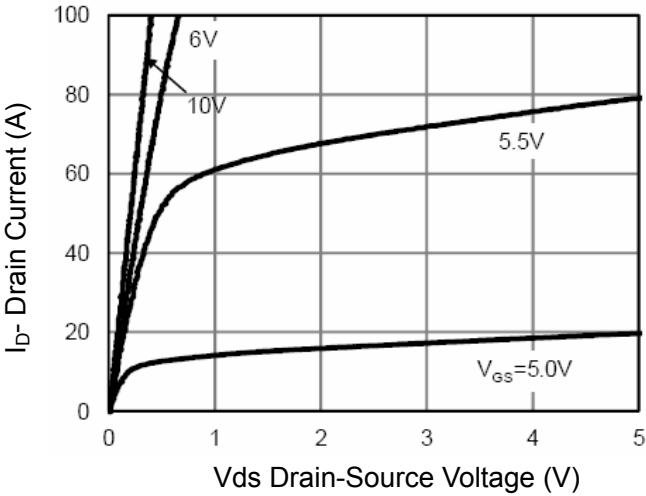


Figure 1 Output Characteristics

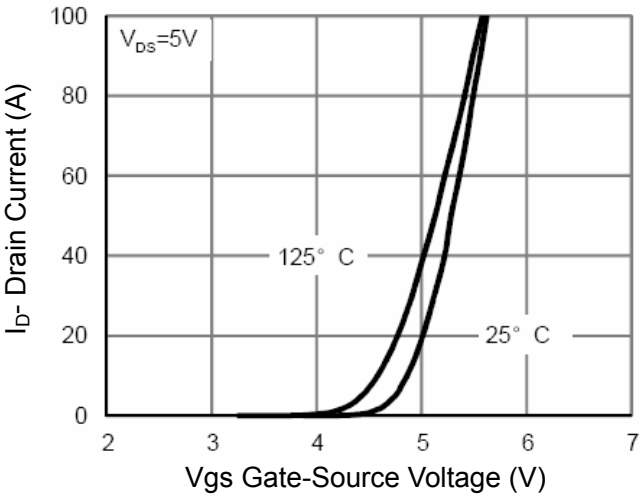


Figure 2 Transfer Characteristics

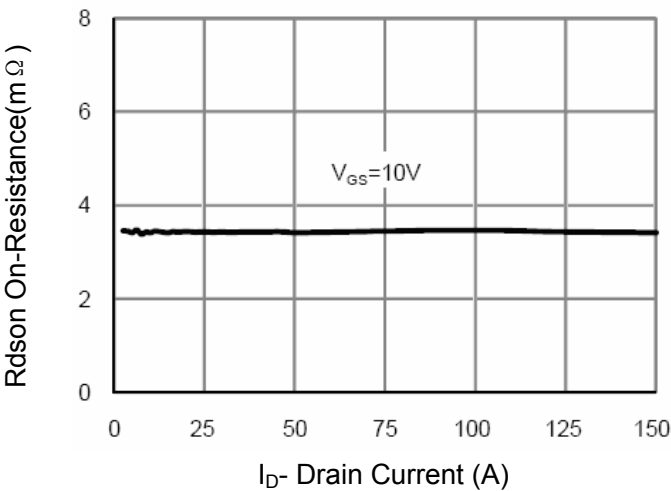


Figure 3 Rdson- Drain Current

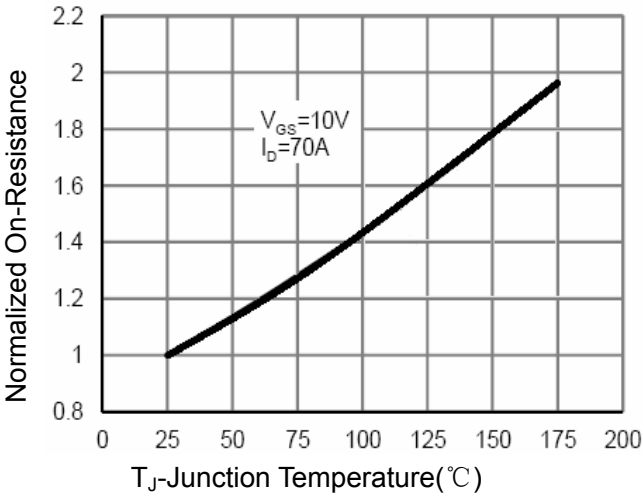


Figure 4 Rdson-Junction Temperature

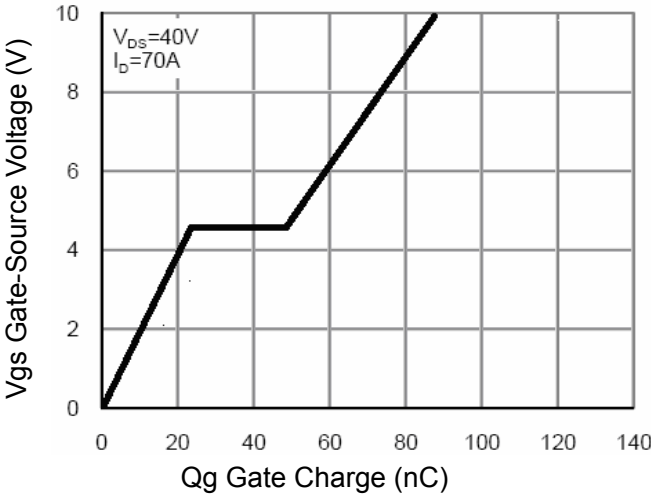


Figure 5 Gate Charge

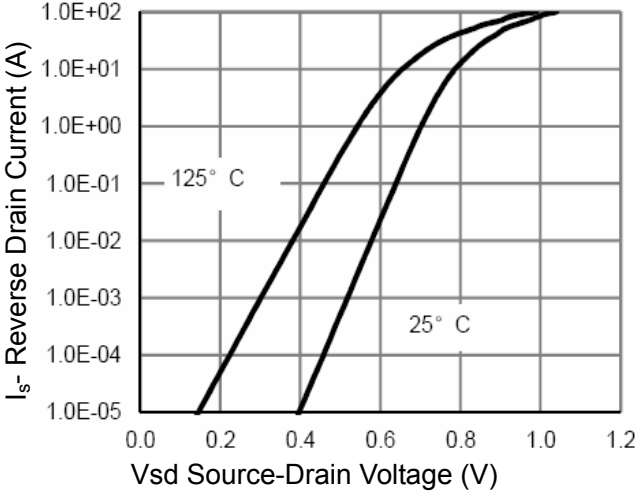


Figure 6 Source- Drain Diode Forward

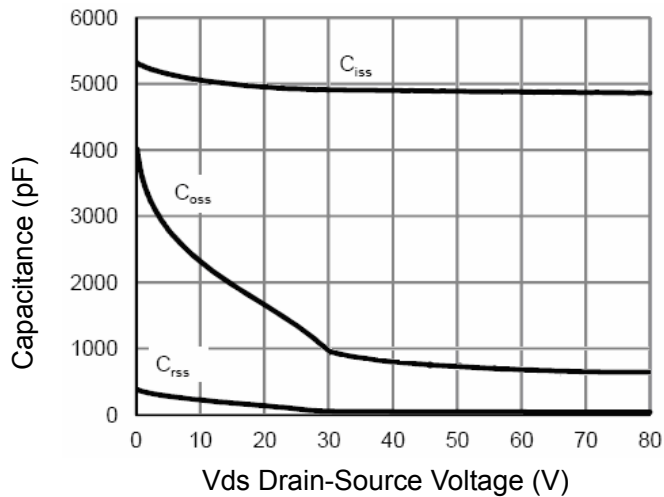


Figure 7 Capacitance vs Vds

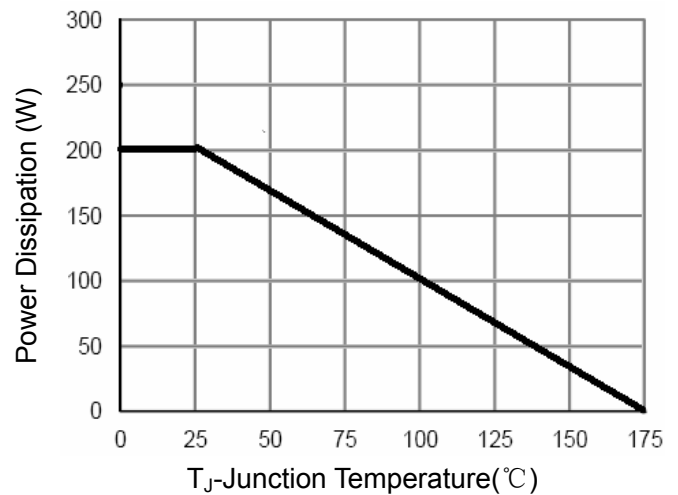


Figure 9 Power De-rating

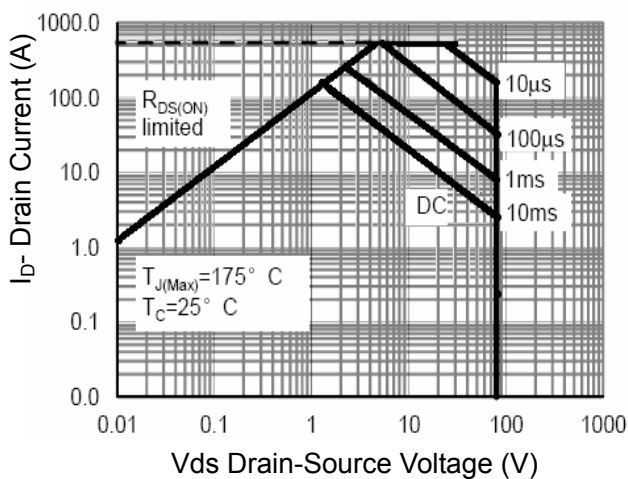


Figure 8 Safe Operation Area

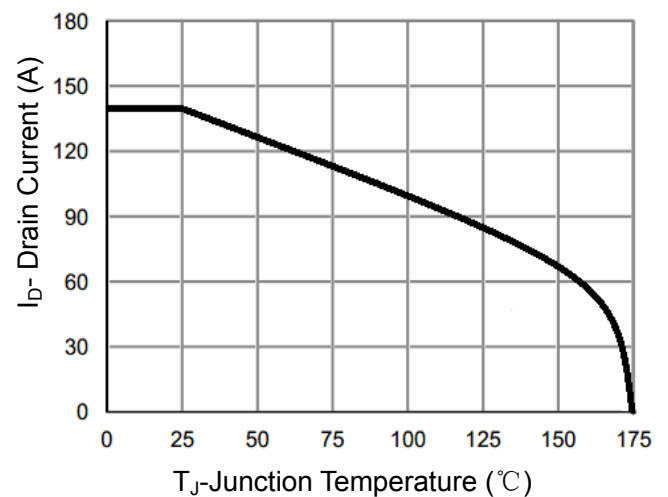


Figure 10 Current De-rating

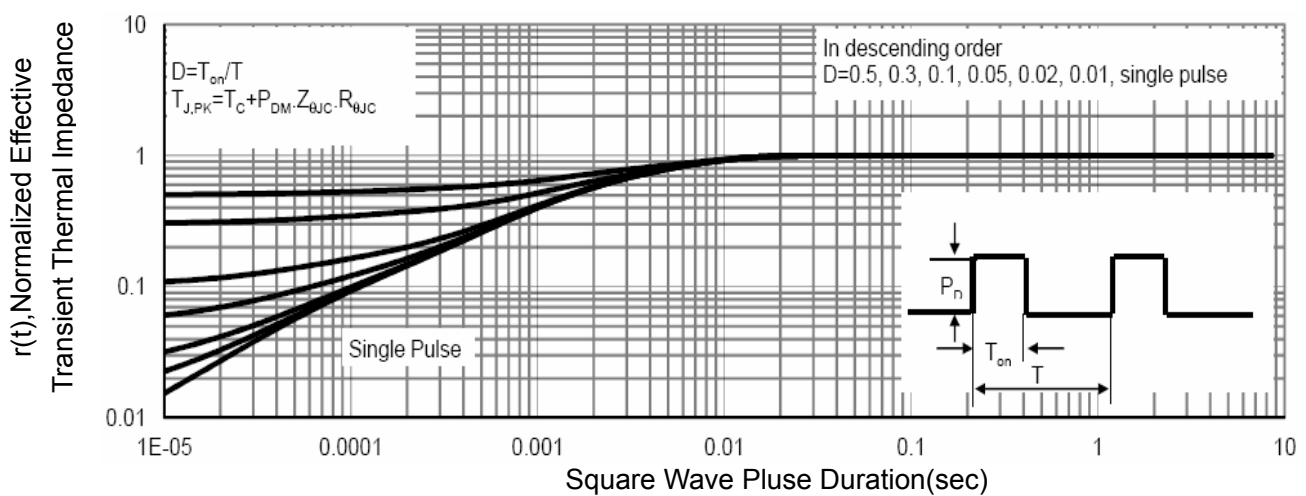
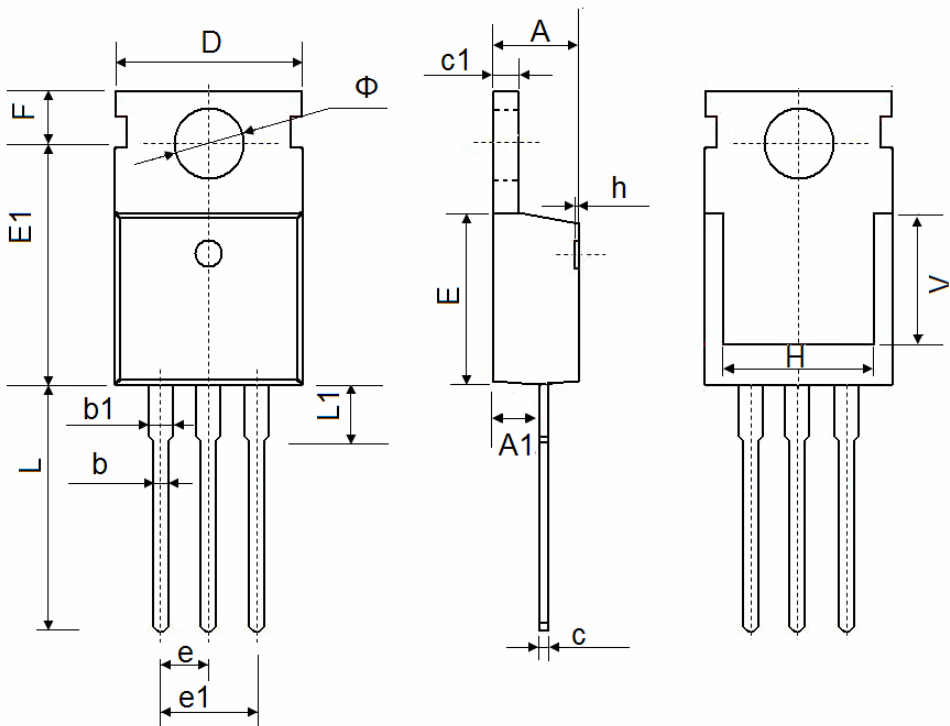


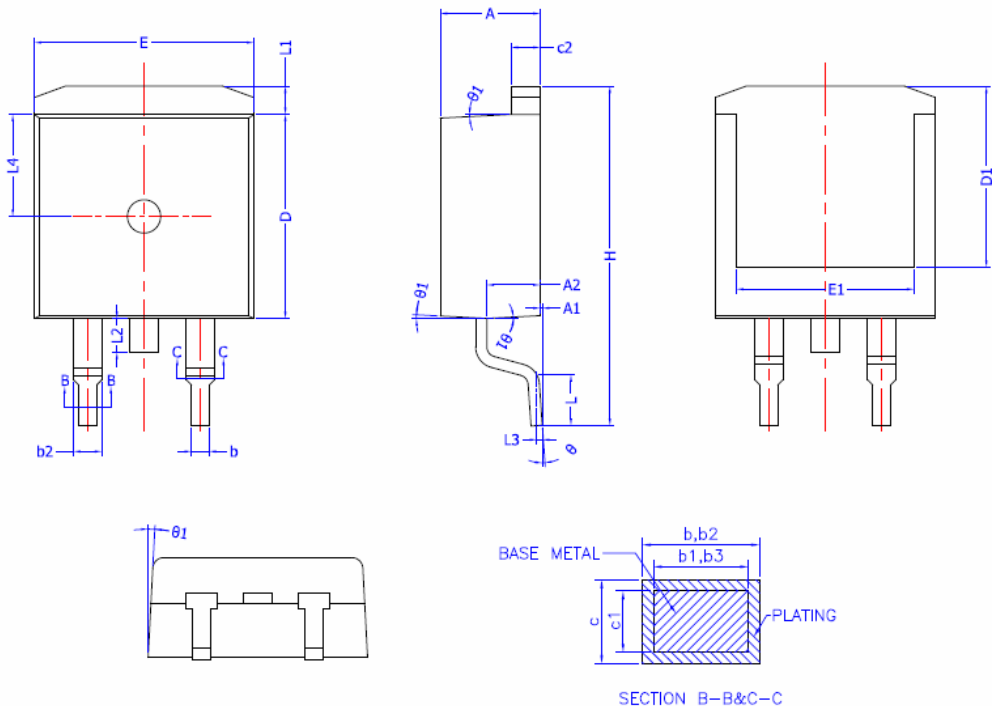
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150

TO-263-2L Package Information



SECTION B-B&C-C

COMMON DIMENSIONS
(UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	—	0.89
b1	0.75	0.80	0.85
b2	1.23	—	1.37
b3	1.22	1.27	1.32
c	0.47	—	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	—	—
E	9.80	9.90	10.00
E1	7.80	—	—
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	—	—	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	—	8°
θ1	1°	3°	5°